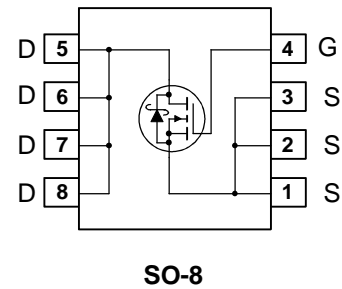


General Description

The FDS6676AS is designed to replace a single SO-8 MOSFET and Schottky diode in synchronous DC:DC power supplies. This 30V MOSFET is designed to maximize power conversion efficiency, providing a low $R_{DS(ON)}$ and low gate charge.



Features

- $V_{DS(V)} = 30V$
- $I_D = 13 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 6m\Omega$ ($V_{GS}=10V$)
- $R_{DS(ON)} < 7.25m\Omega$ ($V_{GS}=4.5V$)
- Includes SyncFET Schottky body diode
- Low gate charge (45nC typical)
- High performance trench technology for
- extremely low $R_{DS(ON)}$ and fast switching
- RoHS Compliant
- High power and current handling capability

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Symbol	Parameter	Rated	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous (Note 1a)	14.5	A
	– Pulsed	50	
P_D	Power Dissipation for Single Operation (Note 1a) (Note 1b) (Note 1c)	2.5	W
		1.2	
		1	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	50	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	25	

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

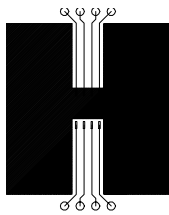
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C		20		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			500	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1	1.5	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C		-4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 14.5\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 13.2\text{ A}$		4.5 5.9	6.0 7.25	m Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	50			A
g_{FS}	Forward Transconductance	$V_{DS} = 10\text{ V}, I_D = 14.5\text{ A}$		66		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		2510		pF
C_{oss}	Output Capacitance			710		pF
C_{riss}	Reverse Transfer Capacitance			270		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.6	2.8	Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		10	20	ns
t_r	Turn-On Rise Time			12	22	ns
$t_{d(off)}$	Turn-Off Delay Time			43	69	ns
t_f	Turn-Off Fall Time			29	46	ns
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\text{ }\Omega$		17	31	ns
t_r	Turn-On Rise Time			22	35	ns
$t_{d(off)}$	Turn-Off Delay Time			34	54	ns
t_f	Turn-Off Fall Time			29	46	ns
$Q_{g(TOT)}$	Total Gate Charge at $V_{GS}=10\text{V}$			45	63	nC
Q_g	Total Gate Charge at $V_{GS}=5\text{V}$	$V_{DD} = 15\text{ V}, I_D = 14.5\text{ A},$		25	35	nC
Q_{gs}	Gate-Source Charge			7		nC
Q_{gd}	Gate-Drain Charge			8		nC

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

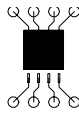
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain–Source Diode Characteristics and Maximum Ratings						
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.5\text{ A}$ (Note 2) $V_{GS} = 0\text{ V}, I_S = 7\text{ A}$ (Note 2)		0.4 0.5	0.7	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 14.5\text{ A},$ $dI_F/dt = 300\text{ A}/\mu\text{s}$ (Note 3)		27		nS
I_{RM}	Diode Reverse Recovery Current			1.9		A
Q_{rr}	Diode Reverse Recovery Charge			26		nC

Notes:

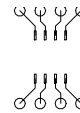
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 50^oW when mounted on a 1 in² pad of 2 oz copper



b) 105^oW when mounted on a .04 in² pad of 2 oz copper



Typical Characteristics

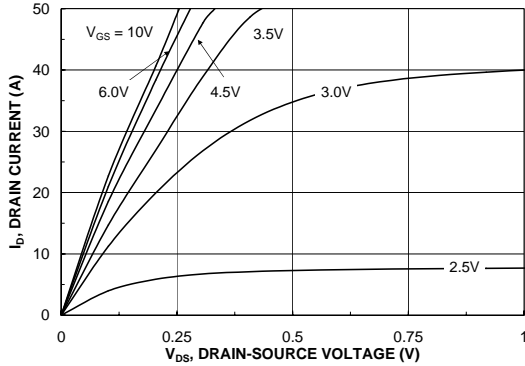


Figure 1. On-Region Characteristics.

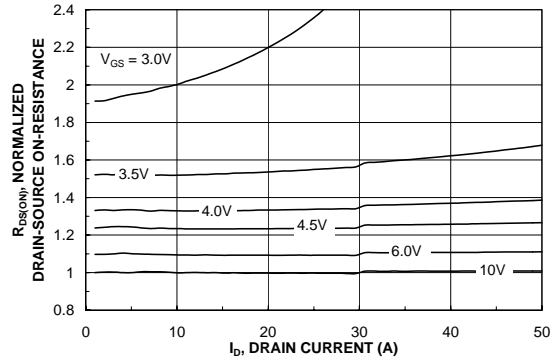


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

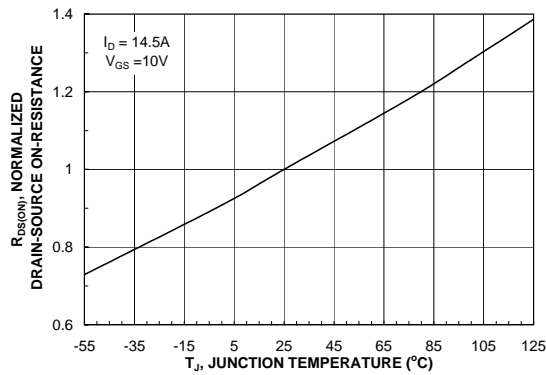


Figure 3. On-Resistance Variation with Temperature.

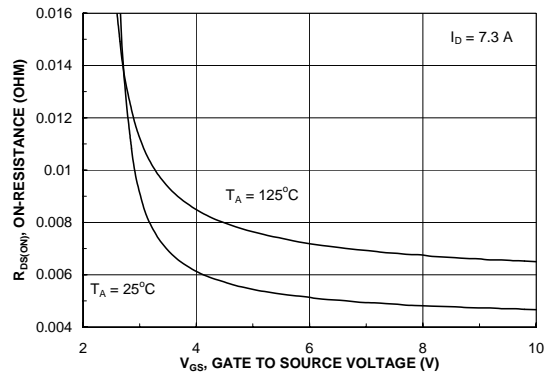


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

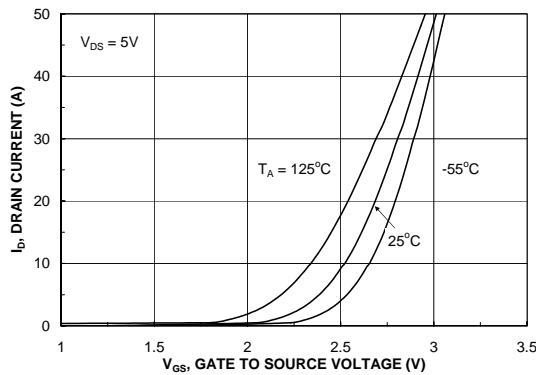


Figure 5. Transfer Characteristics.

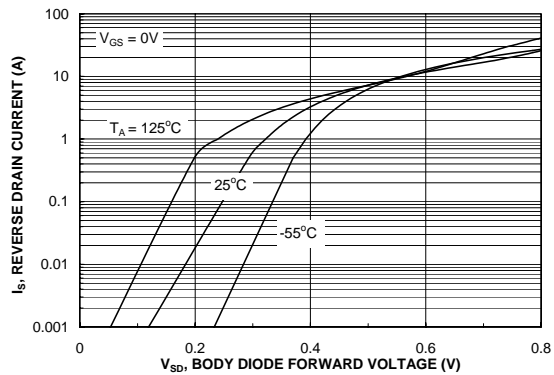


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

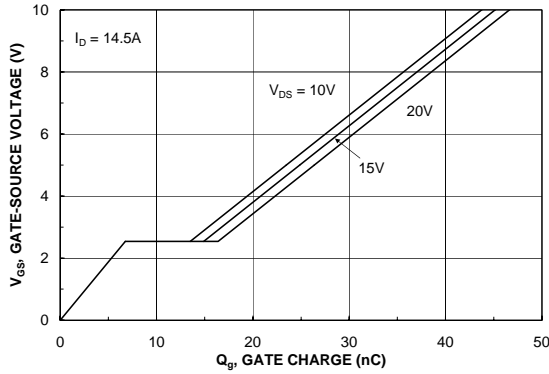


Figure 7. Gate Charge Characteristics.

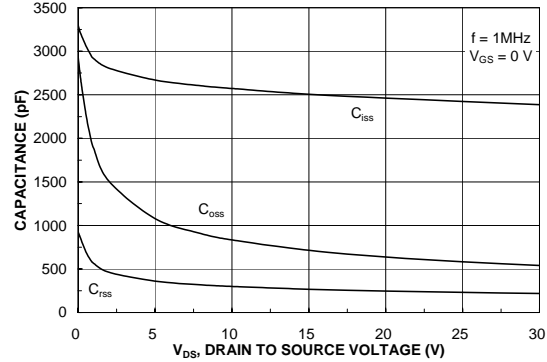


Figure 8. Capacitance Characteristics.

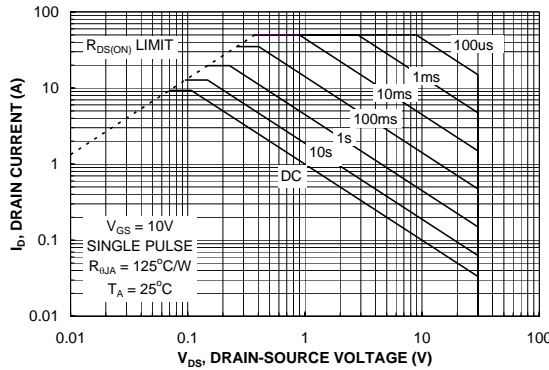


Figure 9. Maximum Safe Operating Area.

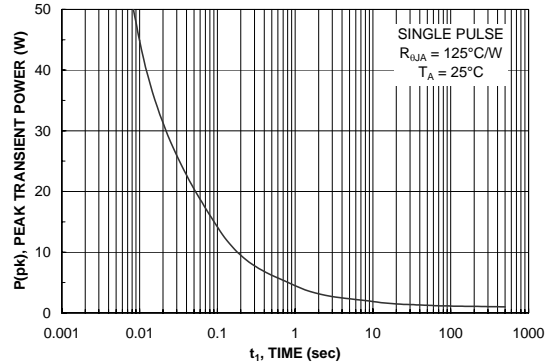


Figure 10. Single Pulse Maximum Power Dissipation.

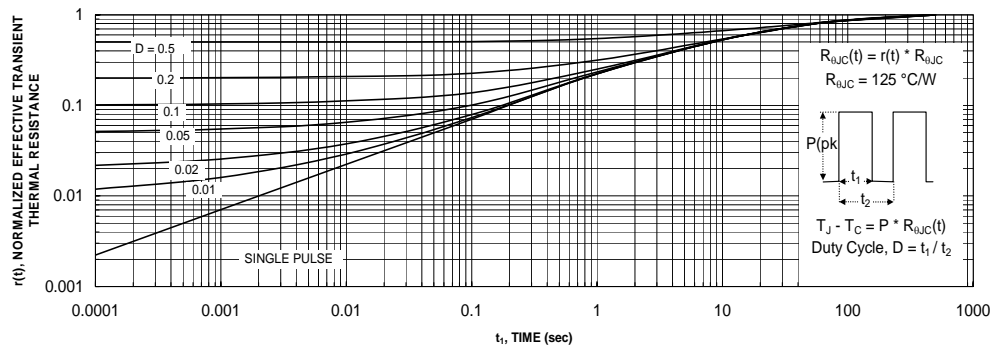


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

Typical Characteristics

SyncFET Schottky Body Diode Characteristics

This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 12 shows the reverse recovery characteristic of the FDS6676AS.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

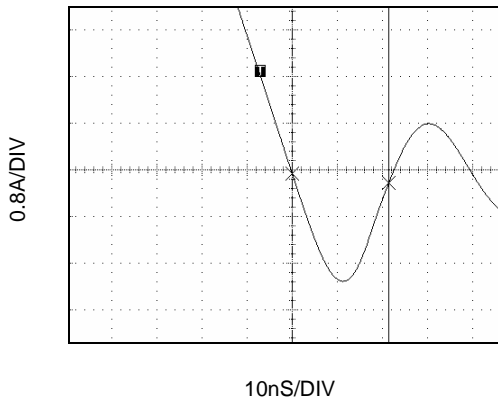


Figure 12. FDS6676AS SyncFET body diode reverse recovery characteristic.

For comparison purposes, Figure 13 shows the reverse recovery characteristics of the body diode of an equivalent size MOSFET produced without SyncFET (FDS6676).

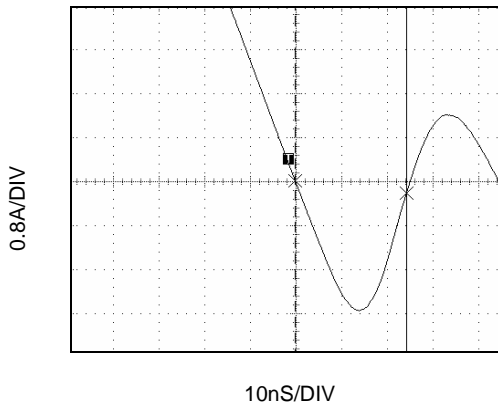


Figure 13. Non-SyncFET (FDS6676) body diode reverse recovery characteristic.

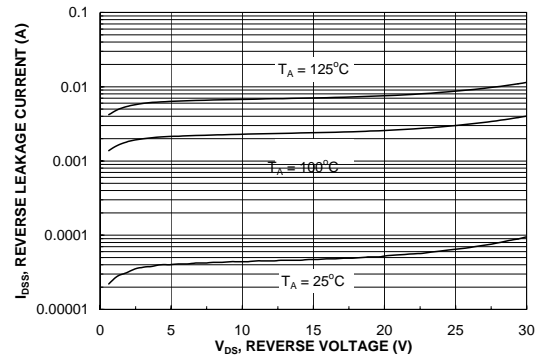
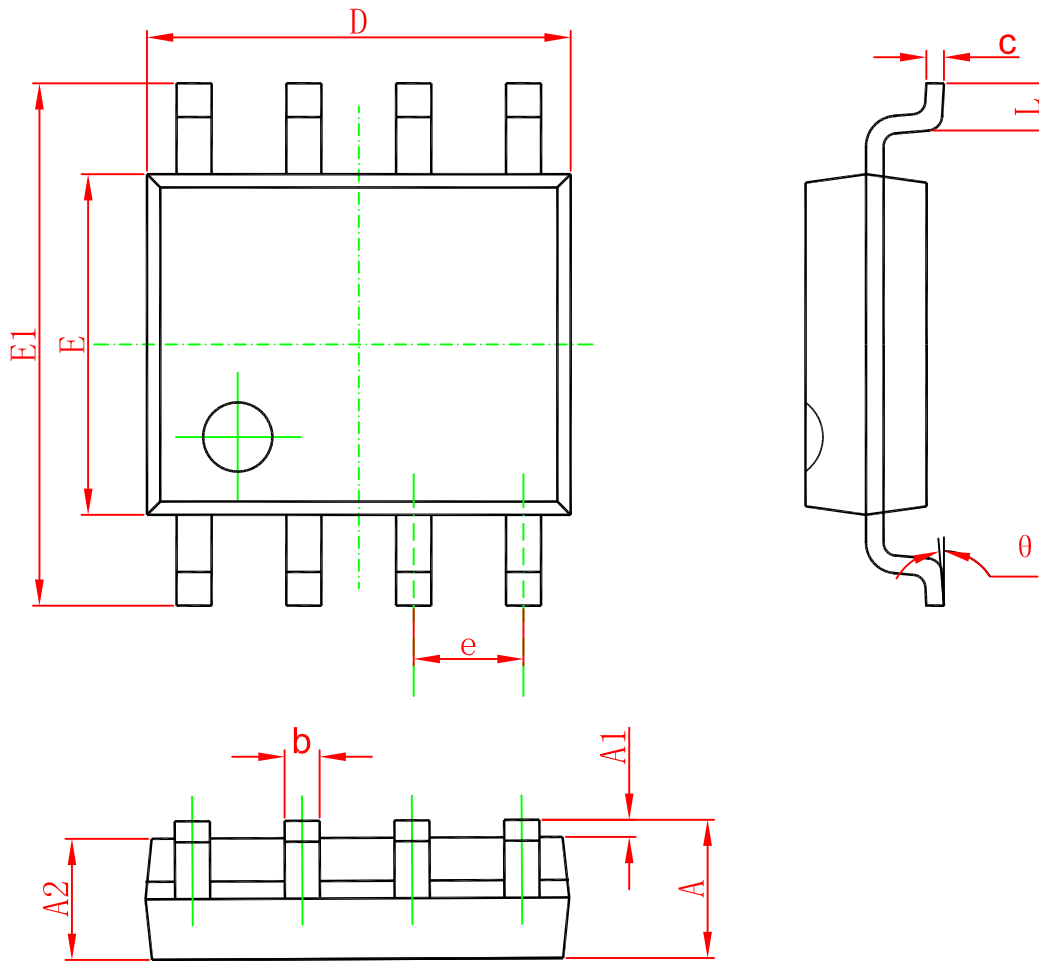


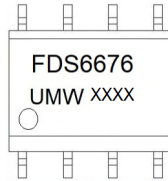
Figure 14. SyncFET body diode reverse leakage versus drain-source voltage and temperature.

Package Mechanical Data SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW FDS6676AS	SOP-8	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>UMW\(友台半导体\)](#)